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STRUCTURE Silicon Monolithic Integrated Circuit

NAME OF PRODUCT DC-AC Inverter Control IC

TYPE BD9890F

FUNCTION • 2ch control with Push-Pull

- Lamp current and voltage sense feed back control
- · Sequencing easily achieved with Soft Start Control
- Short circuit protection with Timer Latch
- Under Voltage Lock Out
- · Short circuit protection with over voltage
- Mode-selectable the operating or stand-by mode by stand-by pin
- Synchronous operating the other BD9890F or BD9890FV IC's
- BURST mode controlled by PWM and DC input
- 2ch in-phase in BURST mode

OAbsolute Maximum Ratings ($Ta = 25^{\circ}C$)

Parameter	Symbol	Limits	Unit	
Supply Voltage	Vcc	15	V	
Operating Temperature Range	Topr	-40∼+90	°C	
Storage Temperature Range	Tstg	−55 ~ +125	°C	
Power Dissipation	Pd	600*1 (BD9890F)	- mW	
Power Dissipation	ru	850*2 (BD9890FV)		
Maximum Junction Temperature	Tjmax	+125	°C	

^{*1}Pd derate at 6.0mW/°C for temperature above Ta = 25°C (When mounted on a PCB 70.0mm × 70.0mm × 1.6mm)

ORecommended operating condition

Parameter	Symbol	Limits	Unit
Supply voltage	Vcc	5. 0~14. 0	V
CT oscillation frequency	fCT	20~150	kHz
BCT oscillation frequency	fBCT	0.05~0.50	kHz

Status of this document

The Japanese version of this document is the official specification.

Please use the translation version of this document as a reference to expedite understanding of the official version. If these are any uncertainty in translation version of this document, official version takes priority.

 $^{^{*2}}$ Pd derate at 8.5mW/ $^{\circ}$ C for temperature above Ta = 25 $^{\circ}$ C (When mounted on a PCB 70.0mm \times 70.0mm \times 1.6mm)



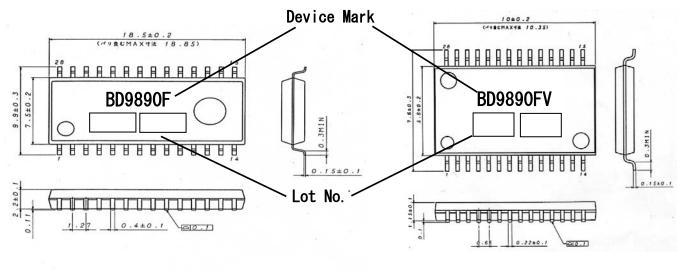
OElectric Characteristics (Ta=25°C, VCC=7V)

			Limits				
Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Conditions	
((WHOLE DEVICE))					I.		
Operating current	Icc1	_	11. 0	17. 0	mA	CT=0. 5V	
Stand-by current	Icc2	_	2	10	μA		
((OVER VOLTAGE DETECT))				•			
FB over voltage detect voltage	Vovf	2. 20	2. 40	2. 60	V		
((STAND BY CONTROL))	_						
Stand-by voltage H	VstH	1. 6	_	Vcc	٧	System ON	
Stand-by voltage L	VstL	-0. 3	_	0.8	٧	System OFF	
Stand-by hysteresis	⊿Vst	0. 08	0.18	0. 28	٧		
((TIMER LATCH))	((TIMER LATCH))						
Timer Latch voltage	Vcp	1. 9	2. 0	2. 1	V		
Timer Latch current	lcp	0. 5	1.0	1.5	μA		
((BURST MODE))							
BOSC Max voltage	VburH	1. 94	2. 0	2. 06	V	fBCT=0. 2kHz	
BOSC Min Voltage	VburL	0. 4	0. 5	0. 6	V	fBCT=0. 2kHz	
BOSC constant current	IBCT	1. 35/BRT	1.5/BRT	1. 65/BRT	A		
BOSC frequency	fB0SC	266	280	294	Hz	BRT=33k Ω 、BCT=0. 050 μ F	
((OSC BLOCK))	1					1	
OSC constant current	ICT	1. 35/RT	1. 5/RT	1. 65/RT	A		
OSC Max voltage	VoscH	1.8	2. 0	2. 2	V	fcT=60kHz	
OSC Min voltage	VoscL	0. 3	0.5	0. 7	٧	fcT=60kHz	
MAX DUTY	MAXDUTY	44	46. 5	49	%	fcT=60kHz	
Soft start current	Iss	1. 0	2. 0	3. 0	μΑ		
IS COMP detect Voltage	Visc	0. 45	0. 50	0. 55	V		
SS COMP detect voltage	Vss	2. 0	2. 2	2. 4	V		
SRT ON resistance	RSRT	_	200	400	Ω		
((UVLO BLOCK))	•	•	•	•			
Operating voltage	Vuv I oH	4. 100	4. 300	4. 500	V		
Shut down voltage	Vuv I oL	3. 900	4. 100	4. 300	٧		
Operating voltage (External UVLO)	Vuv I o 1	2. 160	2. 220	2. 280	V		
Lock out voltage (External UVLO)	Vuv I o 2	2. 242	2. 315	2. 388	V		
Hysteresis width	⊿Vuvlo	0.068	0.095	0. 122	V		
((REG BLOCK))	1					_	
REG output voltage	VREG	3. 038	3. 100	3. 162	٧		
REG source current	IREG	5. 0	-	-	mA	VDEE OREN	
VREF voltage	Vref1	1. 225	1. 250	1. 275	٧	VREF=OPEN	
VREF input voltage range ((FEED BACK BLOCK))	Vref2	0. 60	_	1.50	V	VREF applying voltage	
	V: -1	1 005	1 050	1 075	V	VDEE-ODEN	
IS threshold voltage 1	Vis1	1. 225	1. 250	1. 275	-	VREF=0PEN	
IS threshold voltage 2	Vis2	_	Vref2	_	V	VREF applying voltage	
VS threshold voltage	Vvs	1. 220	1. 250	1. 280	V		
IS source current 1	lis1	_	_	1.5	μA	DUTY=2. OV	
IS source current 2	lis2	13. 0	20. 0	27. 0	μA	DUTY=OV、IS=0.5V	
VS source current	lvs	_	_	1. 0	μA		
((OUTPUT BLOCK))	T		I Was a d	ı			
NAch output voltage H	VoutNAH	Vcc-0. 3	Vcc-0. 1	_	٧		
NBch output voltage H	VoutNBH	Vcc-0. 3	Vcc-0. 1	-	V		
NAch output voltage L NBch output voltage L	VoutNAL VoutNBL	_	0. 1 0. 1	0.3	V		
NAch output sink resistance	RsinkNA		5	0. 3	Ω	laink - 10mA	
NAch output sink resistance NAch output source resistance	RSINKNA	_	8	16	Ω	Isink = 10mA Isource = 10mA	
NBch output sink resistance	RsinkNB	_	5	10	Ω	Isink = 10mA	
NBch output source resistance	RsourceNB	_	8	16	Ω	Isource = 10mA	
Drive output frequency	fout	58. 5	60.0	61. 5	KHz	RT=18kΩ、CT=400pF	
((COMP BLOCK))	1	1 -3.5		1		1	
Under voltage detect	VCOMPL	0. 620	0. 640	0. 660	V		
((PROTECT CLOCK))		3. 020	5. 0.10	1 0.000	<u> </u>	l	
Normal output voltage	VPH	2. 9	3. 1	3. 3	V		
Protect output voltage	VPL	2. 9	J. I —	0.5	V		
Trocoot output vortage	¥FL.	_		0. 0	v		

(This product is not designed to be radiation-resistant.)



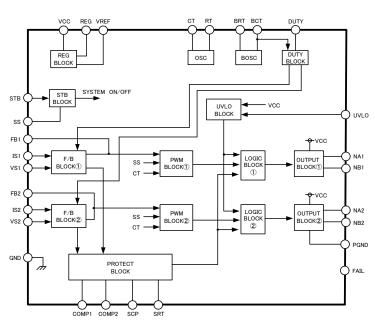
OPackage Dimensions



SOP28 (unit:mm)

SSOP-B28 (unit:mm)

OBlock Diagram



OPin Description

Pin No.	Pin Name	Function
1	DUTY	Control PWM mode and BURST mode
2	BRT	External resistor from BRT to GND for adjusting the BURST triangle oscillator
3	BCT	External capacitor from BCT to GND for adjusting the BURST triangle oscillator
4	RT	External resistor from SRT to RT for adjusting the triangle oscillator
5	SRT	External resistor from SRT to RT for adjusting the triangle oscillator
6	CT	External capacitor from CT to GND for adjusting the triangle oscillator
7	GND	GROUND
8	FB1	Error amplifier output①
9	IS1	Error amplifier input(1)
10	VS1	Error amplifier input②
11	FB2	Error amplifier output②
12	182	Error amplifier input③
13	VS2	Error amplifier input④
14	VREF	Reference voltage
15	FAIL	Protect clock output
16	STB	Stand-by switch
17	COMP1	Under voltage detect for 1ch
18	COMP2	Under voltage detect for 2ch
19	UVL0	External Under Voltage Lock OUT
20	REG	Internal regulator output
21	SS	External capacitor from SS to GND for Soft Start Control
22	SCP	External capacitor from SCP to GND for Timer Latch
23	NA2	FET driver for 2ch
24	NB2	FET driver for 2ch
25	PGND	Ground for FET drivers
26	NB1	FET driver for 1ch
27	NA1	FET driver for 1ch
28	Vcc	Supply voltage input



ONOTE FOR USE

- 1. When designing the external circuit, including adequate margins for variation between external devices and IC. Use adequate margins for steady state and transient characteristics.
- 2. The circuit functionality is guaranteed within of ambient temperature operation range as long as it is within recommended operating range. The standard electrical characteristic values cannot be guaranteed at other voltages in the operating ranges, however the variation will be small.
- 3. Mounting failures, such as misdirection or miscounts, may harm the device.
- 4. A strong electromagnetic field may cause the IC to malfunction.
- 5. The GND pin should be the location within $\pm 0.3V$ compared with the PGND pin.
- 6. BD989OF and BD989OFV incorporate a built-in thermal shutdown circuit (TSD circuit). The thermal shutdown circuit (TSD circuit) is designed only to shut the IC off to prevent runaway thermal operation. It is not designed to protect the IC or guarantee its operation of the thermal shutdown circuit is assumed.
- 7. Absolute maximum ratings are those values that, if exceeded, may cause the life of a device to become significantly shortened. Moreover, the exact failure mode caused by short or open is not defined. Physical countermeasures, such as a fuse, need to be considered when using a device beyond its maximum ratings.
- 8. About the external FET, the parasitic Capacitor may cause the gate voltage to change, when the drain voltage is switching. Make sure to leave adequate margin for this IC variation.
- 9. On operating Slow Start Control (SS is less than 2.2V), It does not operate Timer Latch.
- 1 O. By STB voltage, BD9890F and BD9890FV are changed to 2 states. Therefore, do not input STB pin voltage between one state and the other state $(0.8 \sim 1.6)$.
- 1 1. The pin connected a connector need to connect to the resistor for electrical surge destruction. This IC is a monolithic IC which (as shown is Fig-1) has P⁺ substrate and between the various pins. A P-N junction is formed from this P layer of each pin. For example, the relation between each potential is as follows.
 - \bigcirc (When GND > PinB and GND > PinA, the P-N junction operates as a parasitic diode.)
 - \bigcirc (When PinB > GND > PinA, the P-N junction operates as a parasitic transistor.)

Parasitic diodes can occur inevitably in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits as well as operation faults and physical damage. Accordingly you must not use methods by which parasitic diodes operate, such as applying a voltage that is lower than the GND (P substrate) voltage to an input pin.

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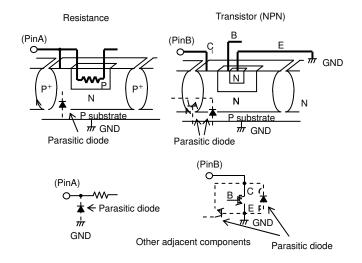


Fig-1 Simplified structure of a Bipolar IC

Notes

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